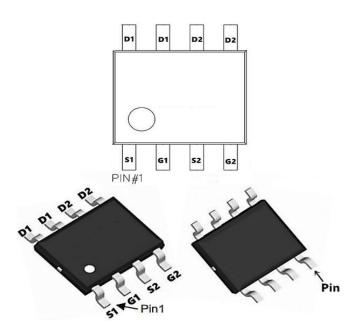


## 40V N+N-Channel Enhancement Mode MOSFET

### **Description**

The SX8H04DF uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



#### **General Features**

 $V_{DS} = 40V I_{D} = 10.8A$ 

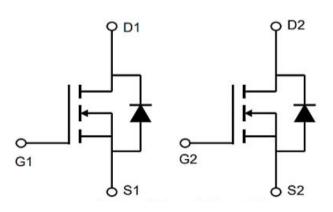
 $R_{DS(ON)} < 20m\Omega$  @  $V_{GS}=10V$ 

#### **Application**

Wireless charging

Boost driver

Brushless motor



### Absolute Maximum Ratings (Tc=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units	
VDS	Drain-Source Voltage	40	V	
VGS	Gate-Source Voltage	±20	V	
lo@Ta=25°C	Continuous Drain Current <sup>1</sup>	10.8	А	
lo@Ta=70°C	Continuous Drain Current <sup>1</sup>	7.6	А	
IDM	Pulsed Drain Current <sup>2</sup>	36	Α	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	31	mJ	
IAS	Avalanche Current	25	Α	
P <b>o@T</b> a=25°C	Total Power Dissipation <sup>4</sup>	1.9	W	
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}$	
TJ	Operating Junction Temperature Range	-55 to 150	${\mathbb C}$	
Reja	Thermal Resistance Junction-ambient¹(t≤10s)	85	°C/W	
Reuc	Thermal Resistance Junction-ambient <sup>1</sup>	8	°C/W	



### 40V N+N-Channel Enhancement Mode MOSFET

### N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , Ip=250uA	40	44		V	
△BVDSS/△TJ	BVDSS Temperature Coefficient	Reference to 25℃, I <sub>D</sub> =1mA		0.034		V/°C	
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	Vgs=10V , ID=5A		16	20		
KD3(ON)	Static Dialii-Source Off-Nesistance-	V <sub>GS</sub> =4.5V , I <sub>D</sub> =4A		20	36	mΩ	
VGS(th)	Gate Threshold Voltage	Vgs=Vps , lp =250uA	1.2	1.6	2.5	V	
$\triangle V$ GS(th)	$V_{GS(th)}$ Temperature Coefficient	VGS-VDS , ID -230UA		-4.56		mV/℃	
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =32V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uA	
1033	Diain-Source Leakage Current	V <sub>DS</sub> =32V , V <sub>GS</sub> =0V , T <sub>J</sub> =55℃		5	5		
IGSS	Gate-Source Leakage Current	Vgs=±20V , Vps=0V			±100	nA	
gfs	Forward Transconductance	VDS=5V , ID=5A		14		S	
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		2.6		Ω	
Qg	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =5A		5.5		nC	
Qgs	Gate-Source Charge			1.25			
$Q_{\mathrm{gd}}$	Gate-Drain Charge			2.5			
Td(on)	Turn-On Delay Time			8.9			
Tr	Rise Time	V <sub>DD</sub> =20V , V <sub>GS</sub> =10V , R <sub>G</sub> =3.3Ω		2.2		ns	
Td(off)	Turn-Off Delay Time	lo=1A		41			
Tf	Fall Time			2.7			
Ciss	Input Capacitance			593			
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		76		pF	
Crss	Reverse Transfer Capacitance			56			
ls	Continuous Source Current <sup>1,5</sup>	V V 0V 5			6.1	Α	
ISM	Pulsed Source Current <sup>2,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			23	Α	
VSD	Diode Forward Voltage <sup>2</sup>	Vgs=0V,Is=1A,TJ=25℃			1.2	V	

#### Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2 . The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3 . The power dissipation is limited by 150  $^{\circ}\mathrm{C}$  junction temperature
- $4\sqrt{100}$  The data is theoretically the same as  $10\sqrt{100}$  and  $10\sqrt{100}$ , in real applications, should be limited by total power dissipation.

2

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### **Typical Characteristics**

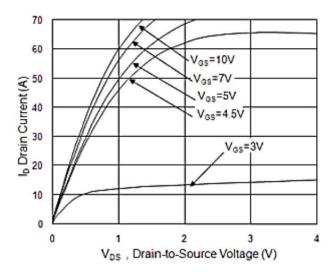


Fig.1 Typical Output Characteristics

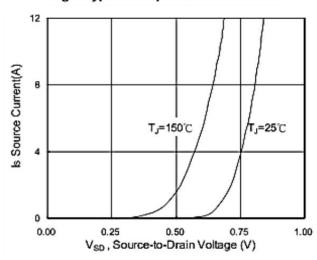


Fig.3 Forward Characteristics of Reverse

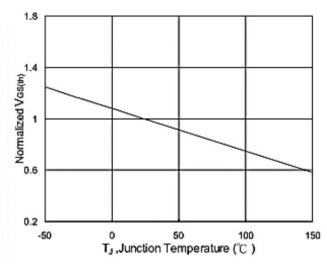


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

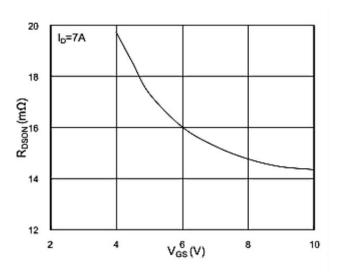


Fig.2 On-Resistance vs. G-S Voltage

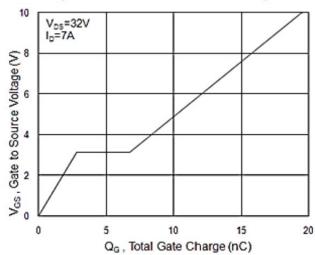


Fig.4 Gate-Charge Characteristics

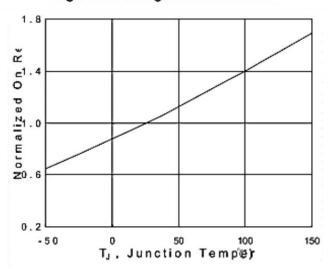
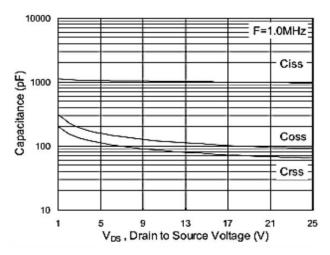


Fig.6 Normalized RDSON vs. TJ



#### **Typical Characteristics**



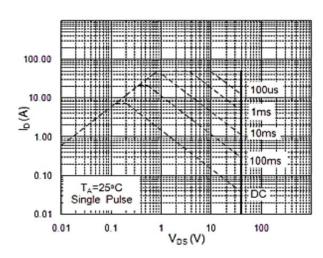


Fig.7 Capacitance

Fig.8 Safe Operating Area

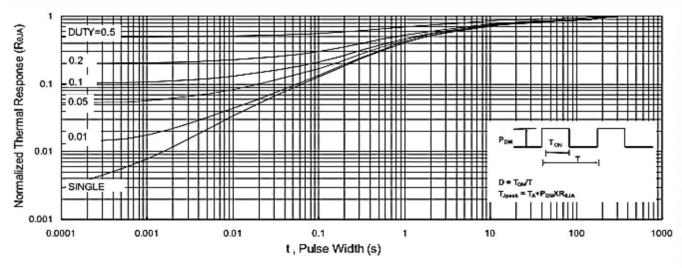


Fig.9 Normalized Maximum Transient Thermal Impedance

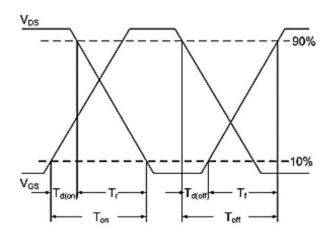


Fig.10 Switching Time Waveform

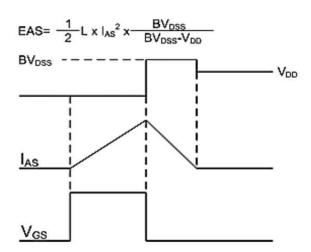
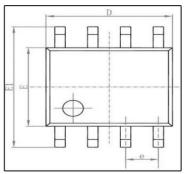


Fig.11 Unclamped Inductive Switching Waveform

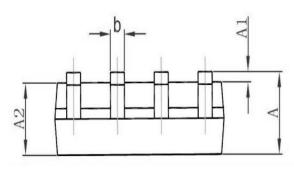




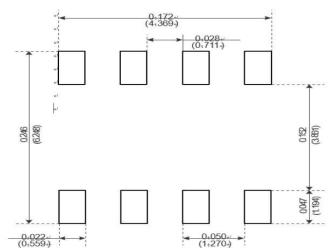
# Package Mechanical Data-SOP-8







C l	Dimensions In	n Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1. 350	1. 750	0. 053	0.069
A1	0. 100	0. 250	0. 004	0.010
A2	1. 350	1. 550	0. 053	0.061
b	0. 330	0. 510	0. 013	0. 020
С	0. 170	0. 250	0.006	0.010
D	4. 700	5. 100	0. 185	0. 200
E	3. 800	4. 000	0. 150	0. 157
E1	5. 800	6. 200	0. 228	0. 244
е	1. 270	(BSC)	0.050	(BSC)
L	0.400	1. 270	0. 016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

### **Package Marking and Ordering Information**

· aonago marning an	a Cracing intermatic	<u> </u>	
Product ID	Pack	Marking	Qty(PCS)
TAPING	SOP-8		3000